

ABSTRACT OF THE DISCLOSURE

This invention proposes a stable magnetic memory device that is equipped with a storage cell having a MTJ, wherein variation in the coercive force (H_c) of a ferromagnetic free layer is suppressed, and a
5 switching characteristic of a bit of a MRAM is improved, and there is no write error. Namely in a magnetic memory device equipped with a first wiring, a second wiring (bit line) intersecting with the first wiring, and a storage cell for writing/reading information of a magnetic spin at an intersecting area of the first wiring and the second wiring, a partial
10 sidewall portion electrically connecting to the storage cell of the second wiring (bit line) has a forward tapered form having a contact angle relative to a top surface of the storage cell being 45 degrees or more.